

Silicon Tuning Diode

- High Q hyperabrupt tuning diode
- Very low capacitance spread
- Designed for low tuning voltage operation for VCO's in mobile communications equipment
- For low frequency control elements such as TCXOS and VCXOS
- High capacitance ratio and good C-V linearity
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101





BBY65-02V

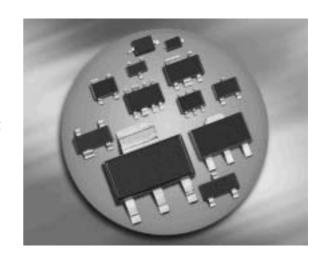


| Туре | Package | Configuration | L _S (nH) | Marking |
|-----------|---------|---------------|----------------------------|---------|
| BBY65-02V | SC79 | single | 0.6 | F |

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|-----------------------------|-----------------|---------|------|
| Diode reverse voltage | V_{R} | 15 | V |
| Forward current | l _F | 50 | mA |
| Operating temperature range | T _{op} | -55 150 | °C |
| Storage temperature | $T_{\rm stg}$ | -55 150 | |

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¹Pb-containing package may be available upon special request



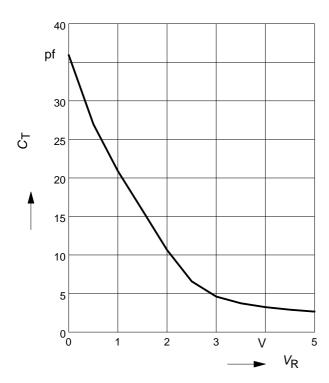
Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

| Parameter | Symbol | | Values | | | |
|---|-------------------------------|------|--------|------|----|--|
| | | min. | typ. | max. | | |
| DC Characteristics | • | • | | | | |
| Reverse current | I _R | | | | nA | |
| <i>V</i> _R = 10 V | | - | - | 10 | | |
| $V_{R} = 10 \text{ V}, \ T_{A} = 85 ^{\circ}\text{C}$ | | - | - | 100 | | |
| AC Characteristics | | | | | | |
| Diode capacitance | C _T | | | | pF | |
| $V_{R} = 0.3 \text{ V}, f = 1 \text{ MHz}$ | | 28.2 | 29.5 | 30.8 | | |
| $V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$ | | - | 20.25 | - | | |
| $V_{R} = 2 \text{ V}, f = 1 \text{ MHz}$ | | - | 9.8 | - | | |
| $V_{R} = 3 \text{ V}, f = 1 \text{ MHz}$ | | - | 4.45 | - | | |
| $V_{R} = 4.7 \text{ V}, f = 1 \text{ MHz}$ | | 2.6 | 2.7 | 2.8 | | |
| Capacitance ratio | C _{T0.3} / | 10 | 10.9 | - | pF | |
| $V_{R} = 0.3 \text{ V}, \ V_{R} = 4.7 \text{ V}$ | C _{T4.7} | | | | | |
| Capacitance ratio | $C_{\text{T1}}/C_{\text{T3}}$ | - | 4.55 | - | pF | |
| $V_{R} = 1 \text{ V}, \ V_{R} = 3 \text{ V}$ | | | | | | |
| Series resistance | r _S | - | 0.6 | 0.9 | Ω | |
| $V_{R} = 1 \text{ V}, f = 470 \text{ MHz}$ | | | | | | |



Diode capacitance $C_T = f(V_R)$

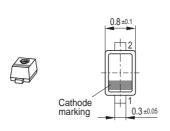
f = 1MHz

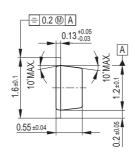


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Package Outline

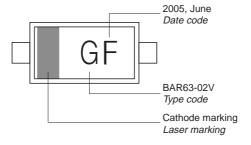




Foot Print



Marking Layout (Example)

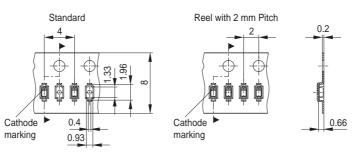


Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel

Reel ø180 mm = 8.000 Pieces/Reel (2 mm Pitch)

Reel ø330 mm = 10.000 Pieces/Reel



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Date Code marking for discrete packages with one digit (SCD80, SC79, SC751) CES-Code

| Month | 2003 | 2004 | 2005 | 2006 | 2007 | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| 01 | а | р | Α | Р | а | р | Α | Р | а | р | Α | Р |
| 02 | b | q | В | Q | b | q | В | Q | b | q | В | Q |
| 03 | С | r | С | R | С | r | С | R | С | r | С | R |
| 04 | d | S | D | S | d | S | D | S | d | S | D | S |
| 05 | е | t | Е | T | е | t | Е | Т | е | t | Е | Т |
| 06 | f | u | F | U | f | u | F | U | f | u | F | U |
| 07 | g | ٧ | G | V | g | ٧ | G | V | g | ٧ | G | V |
| 08 | h | Х | Η | Х | h | Х | Н | Х | h | Х | Η | Х |
| 09 | j | у | 7 | Υ | j | у | 7 | Υ | j | у | J | Υ |
| 10 | k | Z | K | Z | k | Z | K | Z | k | Z | K | Z |
| 11 | I | 2 | L | 4 | ı | 2 | L | 4 | I | 2 | L | 4 |
| 12 | n | 3 | N | 5 | n | 3 | N | 5 | n | 3 | N | 5 |

¹⁾ New Marking Layout for SC75, implemented at October 2005.

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